MN63121

1K-Bit EEPROM

Overview

The MN63121 is a 1K-bit EEPROM supporting serial I/O and operating on a single power supply with a voltage between 1.8 and 5.5 V. It provides the following pins for easy interfacing to microprocessors or microcontrollers: chip select (\overline{CS}), serial clock (\overline{SCK}), data input (DI), data output (DO), reset (RESET), and busy (RDY/ \overline{BUSY}). It includes a built-in timer for use in automatically erasing and writing data during data update operations.

The memory organization is 64×16 bits. The chip indicates the end of a write operation with either the RDY/ \overline{BUSY} pin or the state of the DO pin after the status output mode has been set.

Conversion of peripheral circuits to CMOS realizes great reductions in power consumption. Use of floating gate memory cells and a built-in error correction circuit ensures reliable operation for 10⁵ write cycles.

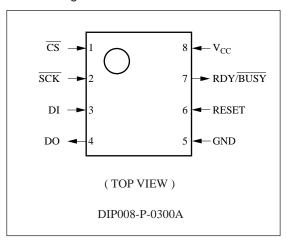
Features

- Memory organization: 64 × 16 bits
- Floating gate memory cells
- Function blocking erroneous writes
- Low power consumption
 - Reads: max. 6.6 mW for $V_{CC} = 3.3 \text{ V}$
 - Standby: max. 66 μW for V_{CC} = 3.3 V
- Built-in self-timer for use in automatically erasing and writing
- Built-in error correction circuit that guarantees 10⁵ write cycles
- 10-year data preservation period

Applications

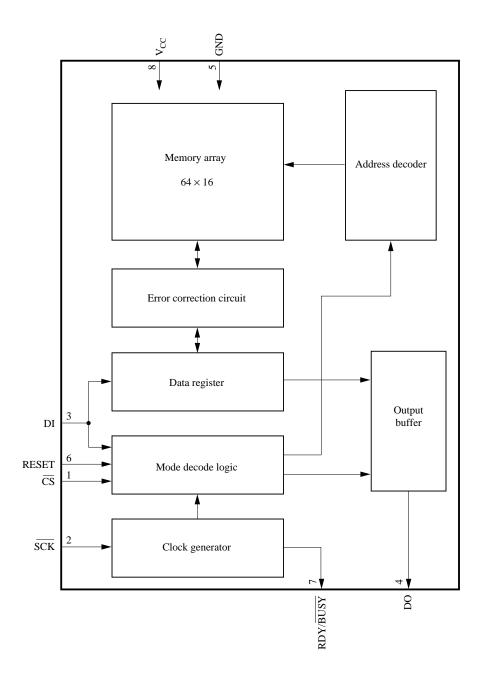
 Keyless entry systems, cordless telephones, storage for recognition and adjustment data for terminals, etc.

■ Pin Assignment



MN63121 Other MOS LSIs

■ Block Diagram



Other MOS LSIs MN63121

■ Pin Descriptions

Pin No.	Symbol	Pin Name
1	CS	Chip select input
2	SCK	Serial clock input
3	DI	Data input
4	DO	Data output
6	RESET	Reset input
7	RDY/BUSY	Busy output

■ Electrical Characteristics

 V_{CC} =1.8 to 5.5V, Ta= $-10^{\circ}C$ to +70 $^{\circ}C$

		Test Conditions	2 to 3 V Operation		5 V Operation		
Parameter	Symbol		min	max	min	max	Unit
Power supply voltage	V _{CC}		1.8	3.3	4.5	5.5	V
Input leakage current at "L" level	I_{LIL}		-10	10	-10	10	μΑ
Input leakage current at "H" level	I_{LIH}		-10	10	-10	10	μΑ
Output leakage current	I_{LO}		_	10	_	10	μΑ
Input voltage at "L" level	V _{IL}		- 0.1	0.2×	- 0.1	0.7	V
			- 0.1	V_{CC}			
Input voltage at "H" level	V_{IH}		0.8×	V _{CC}	3.0	V _{CC}	V
			V _{CC}	+0.3	3.0	+0.3	
V _{CC} power supply current	I_{CC}	SCK=250kHz	_	2.0	_	_	mA
(during operation)		SCK=1MHz	_	_	_	3.0	IIIA
V _{CC} power supply current	I_{SB}	$\overline{\text{CS}}$, $\overline{\text{SCK}}$, DI,	-	20	_	30	μΑ
(during standby)		RESET="H"					
		Other pins open					
Output voltage for "L" level	V _{OL}	I _{OL} =400 μA	_	0.3	_	_	V
(during reads)		I _{OL} =2.1mA	-	_	_	0.45	
Output voltage for "H" level		I - 10A	V _{CC}				V
(during reads)	V _{OH}	I _{OH} =-10 μA	- 0.3	_	_	_	
		Ι _{ΟΗ} =–400 μΑ	_	_	2.4		

■ Function Descriptions

Orders	Code	Address	Data	Function
READ	10101000	$A_0A_1A_2A_3A_4A_500$	$D_0 - D_7 D_8 - D_{15}$	Read from address indicated with pins A_0 – A_5
WRITE	10100100	$A_0A_1A_2A_3A_4A_500$	$D_0 - D_7 D_8 - D_{15}$	Write to address indicated with pins $A_0 - A_5$
EWEN	10100011	xxxxxxx		Enable erase/write
EWDS	10100000	XXXXXXX		Disable erase/write
BUSYFG		00xxxxx	0(busy)	Status output busy flag
			1(ready)	
ENFG	10101001	10xxxxxx	0(enable)	Status output write enable flag
	10101001		1(disable)	
ECCFG		01xxxxxx	0(non-correction)	Status output ECC flag
			1(correction)	

Note: x means "don't care".

MN63121 Other MOS LSIs

■ Package Dimensions (Unit:mm)

DIP008-P-0300A

